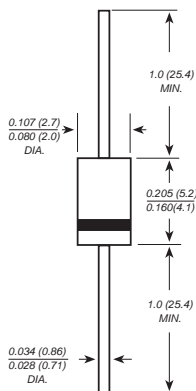


EM513 THRU EM518

GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 1600 to 2000 Volts Forward Current - 1.0 Ampere

DO-41



Dimensions in inches and (millimeters)

FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ Construction utilizes void-free molded plastic technique
- ◆ Low reverse leakage
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-41 molded plastic body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.012 ounce, 0.33 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	EM513	EM516	EM518	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	1600	1800	2000	VOLTS
Maximum RMS voltage	V_{RMS}	1120	1260	1400	VOLTS
Maximum DC blocking voltage	V_{DC}	1600	1800	2000	VOLTS
Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=75^\circ\text{C}$	$I_{(AV)}$	1.0			Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0			Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1			Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	5.0 50.0			mA
Typical junction capacitance (NOTE 1)	C_J	15.0			pF
Typical thermal resistance (NOTE 2)	R_{qJA}	50.0			°C/W
Operating junction and storage temperature range	T_J, T_{STG}	-65 to +175			°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted